Supplementary Information

Fabrication of graphene wrapping ZnIn₂S₄ microspheres heterojunction with enhanced interfacial contact and its improved photocatalytic performance

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UV-vis absorbance spectrum of as-prepared ZnIn₂S₄



Figure S1. UV-vis absorbance spectrum of as-prepared ZnIn₂S₄.

Caculation of electron affinity of ZnIn₂S₄

In general, the electron affinity of semiconductor was equal to the conduction band potential *vs* vacuum level.

The conduction band edge potential (E_{CB}) of $ZnIn_2S_4$ was calculated to be -0.75 eV

(vs NHE) according to the empirical equations: $E_{CB} = E_{VB}-E_g$ and $E_{VB} = X-E_e + 0.5$ E_g;

where E_{VB} is the valence band edge potential;

X is the electronegativity of the semiconductor (4.82 eV for $ZnIn_2S_4$);

 E_e is the energy of free electrons on the hydrogen scale (~4.5 eV);

 $E_{\rm g},$ the band gap energy of the $ZnIn_2S_4,$ is 2.15 eV in our experiment.

Therefore, the electron affinity of $ZnIn_2S_4$ is 3.75 eV.

Energy-Dispersive Spectroscopy (EDS) of $ZnIn_2S_4$

Figure S2. The selected area of EDS

Elt.	Line	Intensity	Conc	Units	Error	MDL	
		(c/s)			2-sig	3-sig	
S	Ka	420.37	26.376	wt.%	2.160	.900	
Zn	Ka	69.98	15.375	wt.%	4.951	1.193	
In	La	477.73	58.249	wt.%	1.097	.758	
			100.000	wt.%			Total

Table	S 1	FDS	results	of Zn	Ins
Table	D 1.	LDO	results		$\mathbf{m}_{2}\mathbf{o}_{4}$

Raman spectrum of ZnIn₂S₄@2 wt% Gr



Figure S3. Raman spectrum of ZnIn₂S₄@2 wt% Gr